

## **HAT1065T**

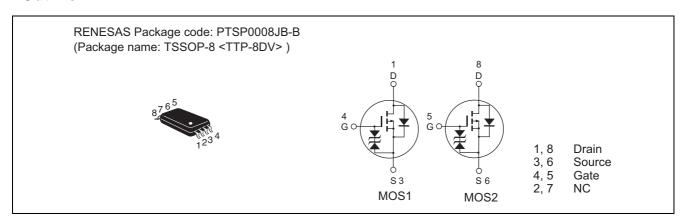
# Silicon P Channel MOS FET High Speed Power Switching

REJ03G0161-0200 Rev.2.00 Aug 06, 2007

#### **Features**

- Low on-resistance
- Capable of –4 V gate drive
- High density mounting

#### **Outline**



#### **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Ratings	Unit
Drain to source voltage	V <sub>DSS</sub>	-200	V
Gate to source voltage	V <sub>GSS</sub>	±15	V
Drain current	I <sub>D</sub>	-0.25	А
Drain peak current	I <sub>D(pulse)</sub> Note1	-1	А
Body-drain diode reverse drain current	I <sub>DR</sub>	-0.25	А
Channel dissipation	Pch Note2	1	W
Channel dissipation	Pch Note3	1.5	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW  $\leq$  10  $\mu$ s, duty cycle  $\leq$  1 %

- 2. 1 Drive operation ; When using the glass epoxy board (FR4 40 x 40 x 1.6 mm), PW  $\leq$  10 s
- 3. 2 Drive operation; When using the glass epoxy board (FR4 40 x 40 x 1.6 mm), PW  $\leq$  10 s

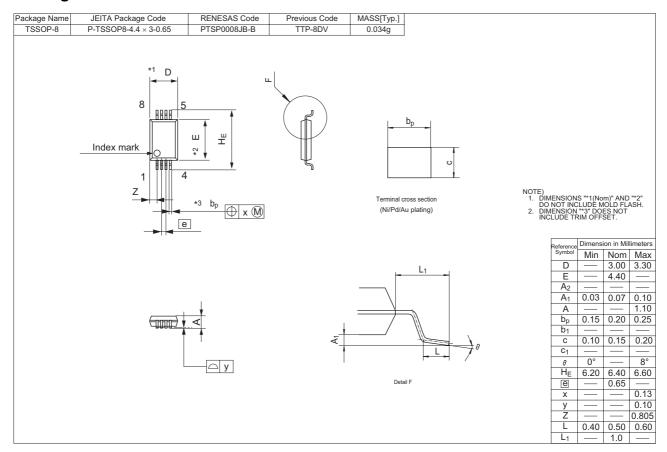
### **Electrical Characteristics**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to source breakdown voltage	V <sub>(BR)DSS</sub>	-200	_	_	V	$I_D = -10 \text{ mA}, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±15		_	V	$I_G = \pm 100 \ \mu A, \ V_{DS} = 0$
Gate to source leak current	I <sub>GSS</sub>	1	1	±10	μΑ	$V_{GS} = \pm 12 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I <sub>DSS</sub>	1	1	-5	μΑ	$V_{DS} = -200 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	-1.0	1	-2.0	<b>V</b>	$V_{DS} = -10 \text{ V}, I_{D} = -1 \text{ mA}$
Static drain to source on state	R <sub>DS(on)</sub>	1	5.0	6.2	Ω	$I_D = -0.25 \text{ A}, V_{GS} = -10 \text{ V}^{\text{Note4}}$
resistance	R <sub>DS(on)</sub>	1	6.0	7.5	Ω	$I_D = -0.25 \text{ A}, V_{GS} = -4 \text{ V}^{\text{Note4}}$
	R <sub>DS(on)</sub>	1	7.0	10.0	Ω	$I_D = -1 A$ , $V_{GS} = -5 V^{Note4}$
Forward transfer admittance	y <sub>fs</sub>	0.29	0.45	_	S	$I_D = -0.25 \text{ A}, V_{DS} = -10 \text{ V}^{\text{Note4}}$
Input capacitance	Ciss	_	140	_	pF	V <sub>DS</sub> = -10 V
Output capacitance	Coss	_	37	_	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	_	10	_	pF	f = 1 MHz
Turn-on delay time	t <sub>d(on)</sub>	_	12	_	ns	$V_{GS} = -5 \text{ V}, I_D = -0.25 \text{ A}$
Rise time	t <sub>r</sub>	_	9	_	ns	$V_{DD} \cong -30 \text{ V}$
Turn-off delay time	t <sub>d(off)</sub>		25		ns	
Fall time	t <sub>f</sub>		15		ns	
Body-drain diode forward voltage	$V_{DF}$		-0.9	-1.4	V	$I_F = -0.25 \text{ A}, V_{GS} = 0^{\text{Note4}}$

Notes: 4. Pulse test

#### **Package Dimensions**



#### **Ordering Information**

Part No.	Quantity	Shipping Container
HAT1065T-EL-E	3000 pcs	Taping

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